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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	37
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 3.6V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560p40l1beabr

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1.5.6 Interrupt controller (INTC)

The interrupt controller (INTC) provides priority-based preemptive scheduling of interrupt requests, suitable for statically scheduled hard real-time systems. The INTC handles 128 selectable-priority interrupt sources.

For high-priority interrupt requests, the time from the assertion of the interrupt request by the peripheral to the execution of the interrupt service routine (ISR) by the processor has been minimized. The INTC provides a unique vector for each interrupt request source for quick determination of which ISR has to be executed. It also provides a wide number of priorities so that lower priority ISRs do not delay the execution of higher priority ISRs. To allow the appropriate priorities for each source of interrupt request, the priority of each interrupt request is software configurable.

When multiple tasks share a resource, coherent accesses to that resource need to be supported. The INTC supports the priority ceiling protocol (PCP) for coherent accesses. By providing a modifiable priority mask, the priority can be raised temporarily so that all tasks which share the same resource can not preempt each other.

The INTC provides the following features:

- Unique 9-bit vector for each separate interrupt source
- 8 software triggerable interrupt sources
- 16 priority levels with fixed hardware arbitration within priority levels for each interrupt source
- Ability to modify the ISR or task priority: modifying the priority can be used to implement the priority ceiling protocol for accessing shared resources.
- 1 external high priority interrupt (NMI) directly accessing the main core and I/O processor (IOP) critical interrupt mechanism

1.5.7 System status and configuration module (SSCM)

The system status and configuration module (SSCM) provides central device functionality.

The SSCM includes these features:

- System configuration and status
 - Memory sizes/status
 - Device mode and security status
 - Determine boot vector
 - Search code flash for bootable sector
 - DMA status
- Debug status port enable and selection
- Bus and peripheral abort enable/disable

The RC oscillator provides these features:

- Nominal frequency 16 MHz
- ±5% variation over voltage and temperature after process trim
- Clock output of the RC oscillator serves as system clock source in case loss of lock or loss of clock is detected by the PLL
- RC oscillator is used as the default system clock during startup

1.5.12 Periodic interrupt timer (PIT)

The PIT module implements these features:

- 4 general-purpose interrupt timers
- 32-bit counter resolution
- Clocked by system clock frequency
- Each channel usable as trigger for a DMA request

1.5.13 System timer module (STM)

The STM implements these features:

- One 32-bit up counter with 8-bit prescaler
- Four 32-bit compare channels
- Independent interrupt source for each channel
- Counter can be stopped in debug mode

1.5.14 Software watchdog timer (SWT)

The SWT has the following features:

- 32-bit time-out register to set the time-out period
- Programmable selection of window mode or regular servicing
- Programmable selection of reset or interrupt on an initial time-out
- Master access protection
- Hard and soft configuration lock bits
- Reset configuration inputs allow timer to be enabled out of reset

1.5.15 Fault collection unit (FCU)

The FCU provides an independent fault reporting mechanism even if the CPU is malfunctioning.

The FCU module has the following features:

- FCU status register reporting the device status
- Continuous monitoring of critical fault signals
- User selection of critical signals from different fault sources inside the device
- Critical fault events trigger 2 external pins (user selected signal protocol) that can be used externally to reset the device and/or other circuitry (for example, a safety relay)
- Faults are latched into a register

The development support provided includes access to the MCU's internal memory map and access to the processor's internal registers.

The NDI provides the following features:

- Configured via the IEEE 1149.1
- All Nexus port pins operate at V_{DDIO} (no dedicated power supply)
- Nexus Class 1 supports Static debug

1.5.29 Cyclic redundancy check (CRC)

The CRC computing unit is dedicated to the computation of CRC off-loading the CPU. The CRC module features:

- Support for CRC-16-CCITT (x25 protocol):
 - $x^{16} + x^{12} + x^5 + 1$
- Support for CRC-32 (Ethernet protocol):

$$-x^{32}+x^{26}+x^{23}+x^{22}+x^{16}+x^{12}+x^{11}+x^{10}+x^8+x^7+x^5+x^4+x^2+x+1$$

 Zero wait states for each write/read operations to the CRC_CFG and CRC_INP registers at the maximum frequency

1.5.30 IEEE 1149.1 JTAG controller

The JTAG controller (JTAGC) block provides the means to test chip functionality and connectivity while remaining transparent to system logic when not in test mode. All data input to and output from the JTAGC block is communicated in serial format. The JTAGC block is compliant with the IEEE standard.

The JTAG controller provides the following features:

- IEEE test access port (TAP) interface 4 pins (TDI, TMS, TCK, TDO)
- Selectable modes of operation include JTAGC/debug or normal system operation.
- 5-bit instruction register that supports the following IEEE 1149.1-2001 defined instructions:
 - BYPASS
 - IDCODE
 - EXTEST
 - SAMPLE
 - SAMPLE/PRELOAD
- 5-bit instruction register that supports the additional following public instructions:
 - ACCESS AUX TAP NPC
 - ACCESS_AUX_TAP_ONCE
- 3 test data registers:
 - Bypass register
 - Boundary scan register (size parameterized to support a variety of boundary scan chain lengths)
 - Device identification register
- TAP controller state machine that controls the operation of the data registers, instruction register and associated circuitry

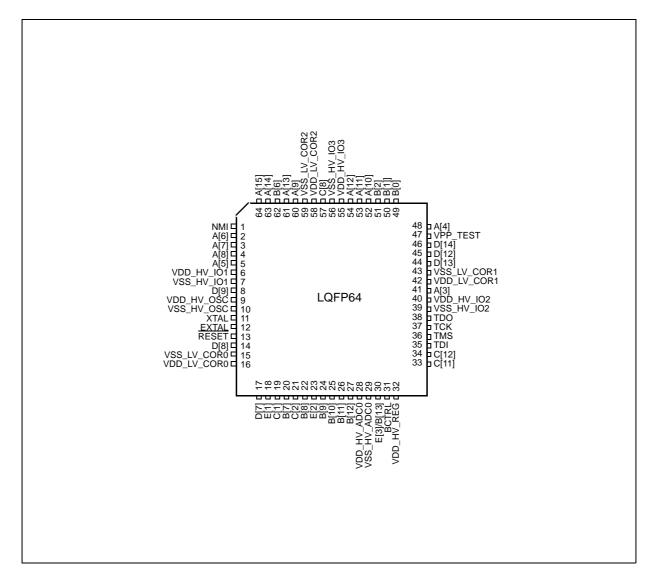


Figure 3. 64-pin LQFP pinout – Airbag configuration (top view)

2.2.3 Pin multiplexing

Table 7 defines the pin list and muxing for the SPC560P34/SPC560P40 devices.

Each row of *Table 7* shows all the possible ways of configuring each pin, via alternate functions. The default function assigned to each pin after reset is the ALT0 function.

SPC560P34/SPC560P40 devices provide three main I/O pad types, depending on the associated functions:

- Slow pads are the most common, providing a compromise between transition time and low electromagnetic emission.
- Medium pads provide fast enough transition for serial communication channels with controlled current to reduce electromagnetic emission.
- Fast pads provide maximum speed. They are used for improved NEXUS debugging capability.

Medium and Fast pads can use slow configuration to reduce electromagnetic emission, at the cost of reducing AC performance. For more information, see "Pad AC Specifications" in the device datasheet.

Table 7. Pin muxing

Port	PCR	Alternate	Functions	Peripheral ⁽³⁾	I/O	Pad sp	peed ⁽⁵⁾	F	Pin		
pin	register	function ^{(1),(2)}	runctions	Peripheral	direc- tion ⁽⁴⁾	SRC = 0	SRC = 1	64-pin	100-pin		
				ALT0	GPIO[0]	SIUL	I/O				
		ALT1	ETC[0]	eTimer_0	I/O						
A[0]	PCR[0]	ALT2	SCK	DSPI_2	I/O	Slow	Medium		51		
		ALT3	F[0]	FCU_0	0						
		_	EIRQ[0]	SIUL	I						
		ALT0	GPIO[1]	SIUL	I/O						
		ALT1	ETC[1]	eTimer_0	I/O						
A[1]	PCR[1]	ALT2	SOUT	DSPI_2	0	Slow	Medium		52		
		ALT3 F[1]	FCU_0	0							
		_	EIRQ[1]	SIUL	I						
		ALT0	GPIO[2]	SIUL	I/O						
		ALT1	ETC[2]	eTimer_0	I/O						
		ALT2		_	_						
A[2]	PCR[2]	ALT3	A[3]	FlexPWM_0	0	Slow	Medium		57		
		_	SIN	DSPI_2	I						
		_	ABS[0]	MC_RGM	I						
		_	EIRQ[2]	SIUL	I						
		ALT0	GPIO[3]	SIUL	I/O						
		ALT1	ETC[3]	eTimer_0	I/O						
A[3]	DCD[3]	ALT2	CS0	DSPI_2	I/O	Slow	Medium	41	64		
A[3]	PCR[3]	PCR[3]	ALT3	B[3]	FlexPWM_0	0	Siow	wealuill	41	04	
		_	ABS[1]	MC_RGM	I						
		_	EIRQ[3]	SIUL	I						

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3 Electrical characteristics

3.1 Introduction

This section contains device electrical characteristics as well as temperature and power considerations.

This microcontroller contains input protection against damage due to high static voltages. However, it is advisable to take precautions to avoid application of any voltage higher than the specified maximum rated voltages.

To enhance reliability, unused inputs can be driven to an appropriate logic voltage level (V_{DD} or V_{SS}). This can be done by the internal pull-up or pull-down resistors, which are provided by the device for most general purpose pins.

The following tables provide the device characteristics and its demands on the system.

In the tables where the device logic provides signals with their respective timing characteristics, the symbol "CC" for Controller Characteristics is included in the Symbol column.

In the tables where the external system must provide signals with their respective timing characteristics to the device, the symbol "SR" for System Requirement is included in the Symbol column.

Caution:

All of the following parameter values can vary depending on the application and must be confirmed during silicon characterization or silicon reliability trial.

3.2 Parameter classification

The electrical parameters are guaranteed by various methods. To give the customer a better understanding, the classifications listed in *Table 8* are used and the parameters are tagged accordingly in the tables where appropriate.

Table 8. Parameter classifications

Classification tag	Tag description
Р	Those parameters are guaranteed during production testing on each individual device.
С	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
Т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

Note: The classification is shown in the column labeled "C" in the parameter tables where appropriate.

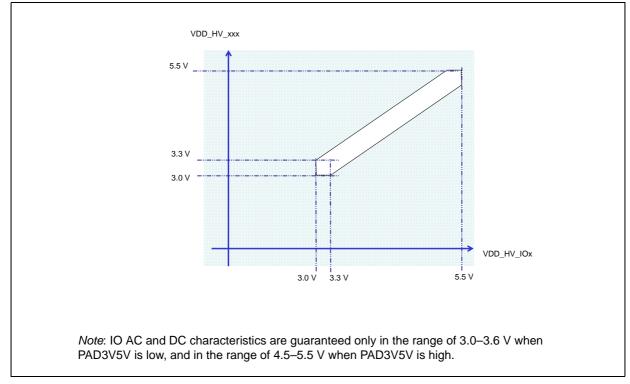


Figure 8. Power supplies constraints (3.0 V \leq V_{DD_HV_IOx} \leq 5.5 V)

The SPC560P34/SPC560P40 supply architecture allows the ADC supply to be managed independently from the standard V_{DD_HV} supply. *Figure 9* shows the constraints of the ADC power supply.

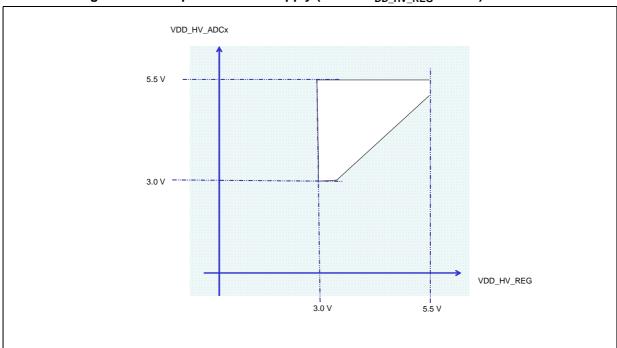


Figure 9. Independent ADC supply (3.0 V \leq V_{DD HV REG} \leq 5.5 V)

3.6 Electromagnetic interference (EMI) characteristics

Table 13. EMI testing specifications

Symbol	Parameter	Conditions	Clocks	Frequency	Level (Typ)	Unit
			f _{OSC} = 8 MHz	150 kHz-150 MHz	11	dΒμ
		V _{DD} = 5.0 V; T _A = 25 °C	f _{CPU} = 64 MHz	150–1000 MHz	13	V
		,	No PLL frequency modulation	IEC level	М	_
		missions $V_{DD} = 3.3 \text{ V; } T_{A} = 25 \text{ °C}$	f _{OSC} = 8 MHz	150 kHz-150 MHz	8	dΒμ
			f _{CPU} = 64 MHz ±4% PLL frequency modulation f _{OSC} = 8 MHz f _{CPU} = 64 MHz	150–1000 MHz	12	V
V	Radiated			IEC level	N	_
V _{EME}	emissions			150 kHz-150 MHz	9	dΒμ
				150–1000 MHz	12	V
			No PLL frequency modulation	IEC level	М	_
		Other device configuration, test conditions and EM testing	f _{OSC} = 8 MHz	150 kHz-150 MHz	7	dΒμ
		per standard IEC61967-2	f _{CPU} = 64 MHz	150–1000 MHz	12	V
			±4% PLL frequency modulation	IEC level	N	_

3.7 Electrostatic discharge (ESD) characteristics

Table 14. ESD ratings^{(1),(2)}

Symbol		Parameter	Conditions	Value	Unit	
V _{ESD(HBM)}	S R	Electrostatic discharge (Human Body Model)	_	2000	V	
V	S	Electrostatic discharge (Charged Device Model)		750 (corners)	V	
V _{ESD(CDM)}	R	Electrostatic discharge (Charged Device Model)	_	500 (other)	V	

^{1.} All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.

3.8 Power management electrical characteristics

3.8.1 Voltage regulator electrical characteristics

The internal voltage regulator requires an external NPN ballast, approved ballast list availbale in *Table 15*, to be connected as shown in *Figure 10*. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the $V_{DD_HV_REG}$, BCTRL and $V_{DD_LV_CORx}$ pins to less than L_{Reg} . (refer to *Table 16*).

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^{2.} A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

In particular two different transient periods can be distinguished:

A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call C_P = C_{P1} + C_{P2}), the two capacitances C_P and C_S are in series, and the time constant is

Equation 5

$$\tau_1 = (R_{SW} + R_{AD}) \bullet \frac{C_P \bullet C_S}{C_P + C_S}$$

Equation 5 can again be simplified considering only C_S as an additional worst condition. In reality, the transient is faster, but the A/D converter circuitry has been designed to be robust also in the very worst case: the sampling time T_S is always much longer than the internal time constant:

Equation 6

$$\tau_1 < (R_{SW} + R_{AD}) \cdot C_S \ll T_S$$

The charge of C_{P1} and C_{P2} is redistributed also on C_S , determining a new value of the voltage V_{A1} on the capacitance according to *Equation 7*:

Equation 7

$$V_{A1} \bullet (C_S + C_{P1} + C_{P2}) = V_A \bullet (C_{P1} + C_{P2})$$

A second charge transfer involves also C_F (that is typically bigger than the on-chip capacitance) through the resistance R_L: again considering the worst case in which C_{P2} and C_S were in parallel to C_{P1} (since the time constant in reality would be faster), the time constant is:

Equation 8

$$\tau_2 < R_L \bullet (C_S + C_{P1} + C_{P2})$$

In this case, the time constant depends on the external circuit: in particular imposing that the transient is completed well before the end of sampling time T_S , a constraints on R_1 sizing is obtained:

Equation 9

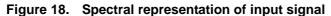
$$8.5 \bullet \tau_2 = 8.5 \bullet R_L \bullet (C_S + C_{P1} + C_{P2}) < T_S$$

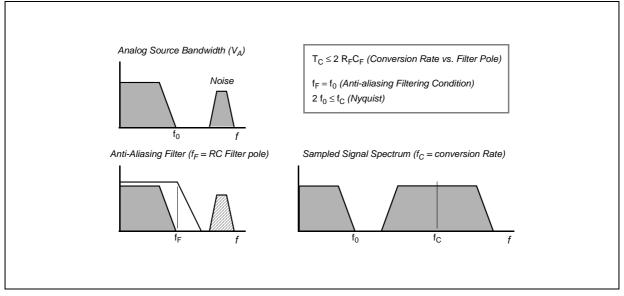
Of course, R_L shall be sized also according to the current limitation constraints, in combination with R_S (source impedance) and R_F (filter resistance). Being C_F definitively bigger than C_{P1} , C_{P2} and C_S , then the final voltage V_{A2} (at the end of the charge transfer transient) will be much higher than V_{A1} . Equation 10 must be respected (charge balance assuming now C_S already charged at V_{A1}):

Equation 10

$${\rm V}_{\rm A2} \bullet ({\rm C}_{\rm S} + {\rm C}_{\rm P1} + {\rm C}_{\rm P2} + {\rm C}_{\rm F}) \\ = {\rm V}_{\rm A} \bullet {\rm C}_{\rm F} + {\rm V}_{\rm A1} \bullet ({\rm C}_{\rm P1} + {\rm C}_{\rm P2} + {\rm C}_{\rm S})$$

The two transients above are not influenced by the voltage source that, due to the presence of the R_FC_F filter, is not able to provide the extra charge to compensate the voltage drop on C_S with respect to the ideal source V_A ; the time constant R_FC_F of the filter is very high with respect to the sampling time (T_S) . The filter is typically designed to act as anti-aliasing.





Calling f_0 the bandwidth of the source signal (and as a consequence the cut-off frequency of the anti-aliasing filter, f_F), according to the Nyquist theorem the conversion rate f_C must be at least $2f_0$; it means that the constant time of the filter is greater than or at least equal to twice the conversion period (T_C) . Again the conversion period T_C is longer than the sampling time T_S , which is just a portion of it, even when fixed channel continuous conversion mode is selected (fastest conversion rate at a specific channel): in conclusion it is evident that the time constant of the filter R_FC_F is definitively much higher than the sampling time T_S , so the charge level on C_S cannot be modified by the analog signal source during the time in which the sampling switch is closed.

The considerations above lead to impose new constraints on the external circuit, to reduce the accuracy error due to the voltage drop on C_S ; from the two charge balance equations above, it is simple to derive *Equation 11* between the ideal and real sampled voltage on C_S :

Equation 11

$$\frac{v_A}{v_{A2}} = \frac{c_{P1} + c_{P2} + c_F}{c_{P1} + c_{P2} + c_F + c_S}$$

From this formula, in the worst case (when V_A is maximum, that is for instance 5 V), assuming to accept a maximum error of half a count, a constraint is evident on C_F value:

Equation 12

$$C_F > 2048 \cdot C_S$$

Table 32. Flash memory module life

Symbol	С	Parameter	Conditions	Val	Unit	
Symbol	C	Farameter	Conditions	Min	Тур	Ollit
P/E	С	Number of program/erase cycles per block for 16 KB blocks over the operating temperature range (T _J)	_	100000	_	cycles
P/E	С	Number of program/erase cycles per block for 32 KB blocks over the operating temperature range (T _J)	_	10000	100000	cycles
P/E	С	Number of program/erase cycles per block for 128 KB blocks over the operating temperature range (T _J)	_	1000	100000	cycles
		Minimum data retention at 85 °C	Blocks with 0–1000 P/E cycles	20	_	years
Retention	С		Blocks with 10000 P/E cycles	10	_	years
			Blocks with 100000 P/E cycles	5	_	years

Ambient temperature averaged over duration of application, not to exceed recommended product operating temperature range.

Table 33. Flash memory read access timing

Symbol	С	Parameter	Conditions ⁽¹⁾	Max value	Unit
f	_	Maximum working frequency for code flash memory at given	2 wait states	66	MHz
t _{max}		number of wait states in worst conditions	0 wait states	18	IVII IZ
f _{max}	С	Maximum working frequency for data flash memory at given number of wait states in worst conditions	8 wait states	66	MHz

^{1.} $V_{DD} = 3.3 \text{ V} \pm 10\% / 5.0 \text{ V} \pm 10\%$, $T_A = -40 \text{ to } 125 \,^{\circ}\text{C}$, unless otherwise specified

3.15.2 Flash memory power supply DC characteristics

Table 34 shows the power supply DC characteristics on external supply.

Table 34. Flash memory power supply DC electrical characteristics

Symbol		(Parameter	Conditions ⁽¹⁾		Value		Unit
		C	r arameter	Conditions	Min	Тур	Max	Oiiit
I _{FLPW}	C C	D	Sum of the current consumption on V _{DD_HV_IOx} and V _{DD_LV_CORx} during low-power mode	Code flash memory	_	_	900	μA
1	, с,		Sum of the current consumption on V _{DD_HV_IOx}	Code flash memory	_	_	150	
IFPWD	С		Sum of the current consumption on V _{DD_HV_IOx} and V _{DD_LV_CORx} during power-down mode	Data flash memory	_	_	150	μΑ

^{1.} V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified.

- 4. C_L includes device and package capacitance (C_{PKG} < 5 pF).
- 5. The configuration PAD3V5 = 1 when V_{DD} = 5 V is only transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

3.17.2 IEEE 1149.1 interface timing

Table 38. JTAG pin AC electrical characteristics

No	Symbo		С	Parameter	Conditions	Va	lue	Unit
-	Syllibo	1	C	raiametei	Conditions	Min	Max	Ollic
1	t _{JCYC}	CC	D	TCK cycle time	_	100	_	ns
2	t _{JDC}	СС	D	TCK clock pulse width (measured at V _{DD_HV_IOx} /2)	_	40	60	ns
3	t _{TCKRISE}	СС	D	TCK rise and fall times (40%–70%)	_	_	3	ns
4	$t_{\rm TMSS}, t_{\rm TDIS}$	CC	D	TMS, TDI data setup time	_	5	_	ns
5	t _{TMSH,} t _{TDIH}	СС	D	TMS, TDI data hold time	_	25	_	ns
6	t _{TDOV}	СС	D	TCK low to TDO data valid	_	_	40	ns
7	t _{TDOI}	СС	D	TCK low to TDO data invalid	_	0	_	ns
8	t _{TDOHZ}	CC	D	TCK low to TDO high impedance	_	40	_	ns
9	t _{BSDV}	СС	D	TCK falling edge to output valid	_	_	50	ns
10	t _{BSDVZ}	СС	D	TCK falling edge to output valid out of high impedance	_	_	50	ns
11	t _{BSDHZ}	СС	D	TCK falling edge to output high impedance	_	_	50	ns
12	t _{BSDST}	СС	D	Boundary scan input valid to TCK rising edge	_	50	—	ns
13	t _{BSDHT}	СС	D	TCK rising edge to boundary scan input invalid	_	50		ns

Figure 22. JTAG test clock input timing

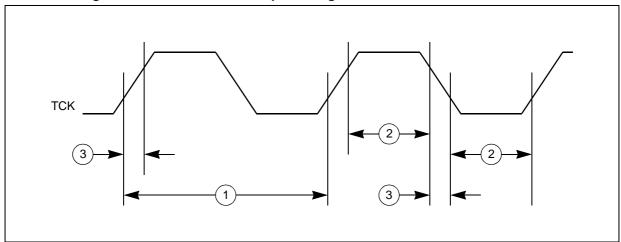


Figure 25. Nexus output timing

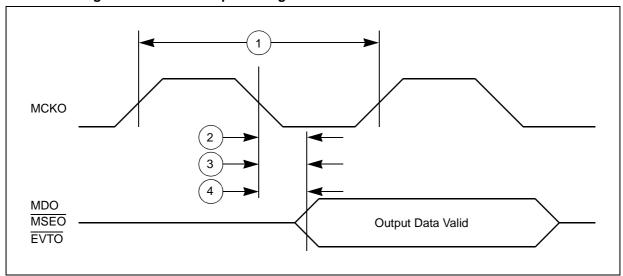
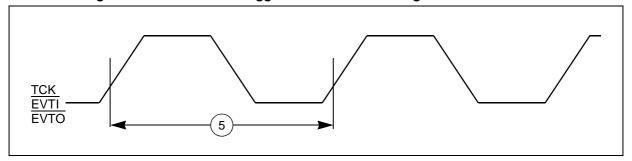


Figure 26. Nexus event trigger and test clock timing



IRQ 1

Figure 28. External interrupt timing

3.17.5 DSPI timing

Table 41. DSPI timing⁽¹⁾

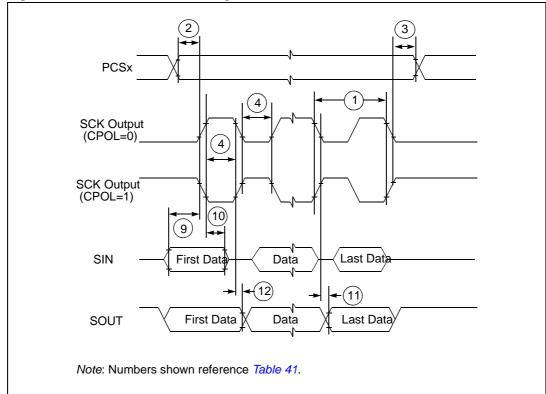
Iabit	; 41.	וטט	1 (111	ning` ′							
No.	Symi	h a l	С	Parameter	Conditions	Val	ue	Unit			
NO.	Syllii	DOI	C	Farameter	Conditions	Min Max		Unit			
1	4	СС	D	DSPI cycle time	Master (MTFE = 0)	60	_	no			
•	t _{SCK}	CC	D	DSFI Cycle time	Slave (MTFE = 0)	60	_	ns			
2	t _{CSC}	СС	D	CS to SCK delay	_	16	_	ns			
3	t _{ASC}	СС	D	After SCK delay	_	26	_	ns			
4	t _{SDC}	СС	D	SCK duty cycle	_	0.4 * t _{SCK}	0.6 * t _{SCK}	ns			
5	t _A	СС	D	Slave access time	SS active to SOUT valid	_	30	ns			
6	t _{DIS}	СС	D	Slave SOUT disable time	SS inactive to SOUT high impedance or invalid	_	16	ns			
7	t _{PCSC}	СС	D	PCSx to PCSS time	_	13	_	ns			
8	t _{PASC}	СС	D	PCSS to PCSx time	_	13	_	ns			
								Master (MTFE = 0)	35	_	
9		СС	6	Data actus tima for innuta	Slave	4	_	ns			
9	^L SUI	t _{SUI} CC	C D	Data setup time for inputs	Master (MTFE = 1, CPHA = 0)	35	_				
					Master (MTFE = 1, CPHA = 1)	35	_				
					Master (MTFE = 0)	- 5	_				
10		00	_	Data hald time for inputs	Slave	4	_				
10	t _{HI}	CC	ט	D Data hold time for inputs	Master (MTFE = 1, CPHA = 0)	11	_	ns			
					Master (MTFE = 1, CPHA = 1)	-5	_				

Table 41. DSPI timing⁽¹⁾ (continued)

No.	Symbol		С	Parameter	Conditions	Value		- Unit	
				Farameter Conditions -		Min	Max		
11	t _{suo}		D	Data valid (after SCK edge)	Master (MTFE = 0)	_	12		
					Slave	_	36	ns	
		СС			Master (MTFE = 1, CPHA = 0)	_	12		
					Master (MTFE = 1, CPHA = 1)	_	12		
	t _{HO}		CC D	D Data hold time for outputs	Master (MTFE = 0)	-2	_		
12		CC			Slave	6		ns	
					Master (MTFE = 1, CPHA = 0)	6	_	113	
					Master (MTFE = 1, CPHA = 1)	-2	_		

^{1.} All timing are provided with 50 pF capacitance on output, 1 ns transition time on input signal





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4.2 Package mechanical data

4.2.1 LQFP100 mechanical outline drawing

Figure 38. LQFP100 package mechanical drawing

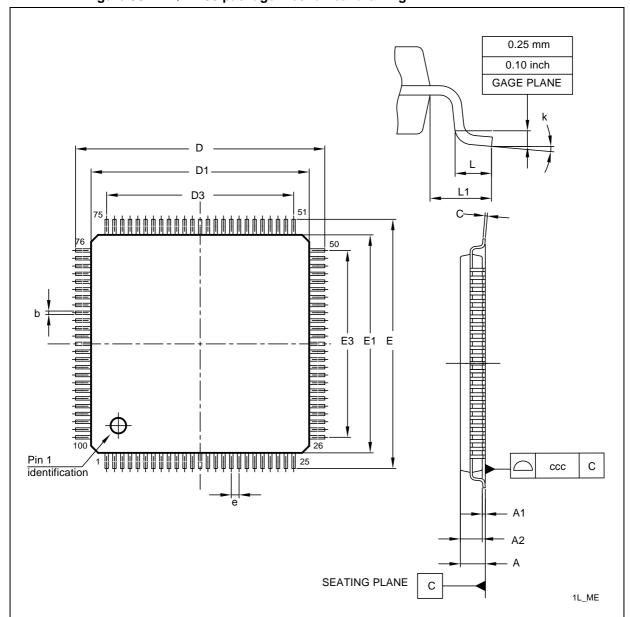


Table 42. LQFP100 package mechanical data

	Dimensions							
Symbol	mm			inches ⁽¹⁾				
	Min	Тур	Max	Min	Тур	Max		
Α	_	_	1.600	_	_	0.0630		
A1	0.050	_	0.150	0.0020	_	0.0059		
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571		
b	0.170	0.220	0.270	0.0067	0.0087	0.0106		
С	0.090	_	0.200	0.0035	_	0.0079		
D	15.800	16.000	16.200	0.6220	0.6299	0.6378		
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591		
D3	_	12.000	_	_	0.4724	_		
Е	15.800	16.000	16.200	0.6220	0.6299	0.6378		
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591		
E3	_	12.000	_	_	0.4724	_		
е	_	0.500	_	_	0.0197	_		
L	0.450	0.600	0.750	0.0177	0.0236	0.0295		
L1	_	1.000	_	_	0.0394	_		
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°		
ccc ⁽²⁾	0.08			0.0031				

^{1.} Values in inches are converted from millimeters (mm) and rounded to four decimal digits.

^{2.} Tolerance

4.2.2 LQFP64 mechanical outline drawing

Figure 39. LQFP64 package mechanical drawing

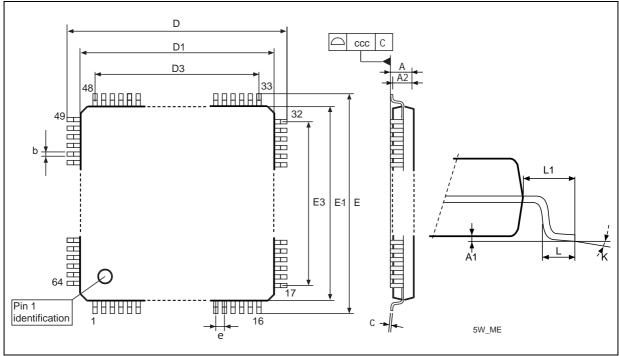


Table 43. LQFP64 package mechanical data

	Dimensions							
Symbol		mm		inches ⁽¹⁾				
	Min	Тур	Max	Min	Тур	Max		
А	_	_	1.6	_	_	0.063		
A1	0.05	_	0.15	0.002	_	0.0059		
A2	1.35	1.4	1.45	0.0531	0.0551	0.0571		
b	0.17	0.22	0.27	0.0067	0.0087	0.0106		
С	0.09	_	0.2	0.0035	_	0.0079		
D	11.8	12	12.2	0.4646	0.4724	0.4803		
D1	9.8	10	10.2	0.3858	0.3937	0.4016		
D3	_	7.5	_	_	0.2953	_		
Е	11.8	12	12.2	0.4646	0.4724	0.4803		
E1	9.8	10	10.2	0.3858	0.3937	0.4016		
E3	_	7.5	_	_	0.2953	_		
е	_	0.5	_	_	0.0197	_		
L	0.45	0.6	0.75	0.0177	0.0236	0.0295		
L1	_	1	_	_	0.0394	_		